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ABSTRACT

This invention provides a method of forming contact holes and via holes in interlevel dielectric which insure good metal stepcoverage. The contact or via holes have tapered sides and smoothed edges. The method uses isotropic etching, anisotropic etching, and argon sputter etching in vacuum and does not require high temperature contact reflow. The final argon sputter etch is a timed etch that smoothes all sharp edges, exposes the regions where electrical contact will be made, and planarizes the interlevel dielectric.

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